MOS FET Power Amplifier Module for E-GSM Handy Phone



ADE-208-434B (Z) 3rd Edition November 1997

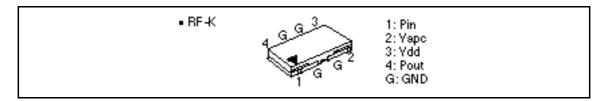
Application

- For E-GSM class4 880 to 915 MHz
- For 3.5 V nominal battery use

Features

- High gain 3stage amplifier : 0 dBm input
- Lead less thin & Small package : 2 mm Max, 0.2cc
- High efficiency : 45% Typ at 35.5 dBm
- Wide gain control range : 70 dB Typ

Pin Arrangement



Absolute Maximum Ratings ($Tc = 25^{\circ}C$)

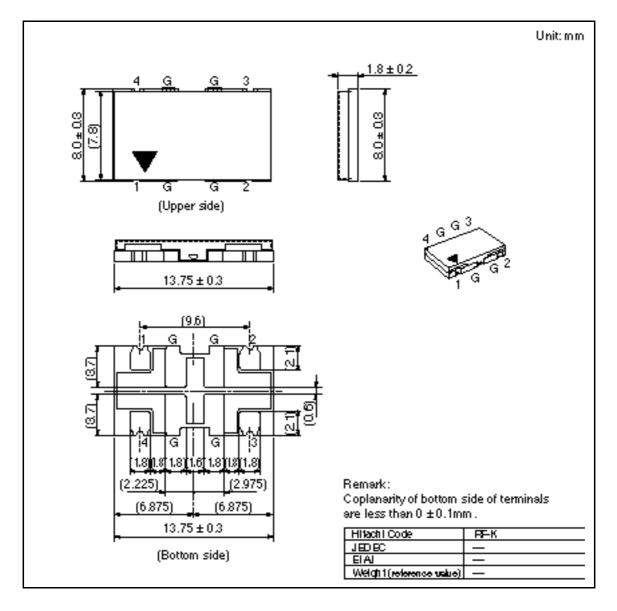
Item	Symbol	Rating	Unit	
Supply voltage	V _{dd}	8	V	
Supply current	I _{DD}	3	А	
V _{APC} voltage	V _{APC}	4	V	
Input power	Pin	10	mW	
Operating case temperature	Tc (op)	-30 to +100	°C	
Storage temperature	Tstg	-30 to +100	°C	
Output power	Pout	5	W	



Item	Symbol	Min	Тур	Max	Unit	Test Condition
Frequency range	f	880		915	MHz	
Control voltage range	V_{APC}	0.5		2.2	V	
Drain cutoff current	I _{DS}		_	100	μA	$V_{DD} = 8 \text{ V}, V_{APC} = 0 \text{ V}$
Total efficiency	т	40	45	_	%	Pin = 0 dBm, V_{DD} = 3.5 V,
2nd harmonic distortion	2nd H.D.		-45	-35	dBc	Pout = 35.5 dBm,
3rd harmonic distortion	3rd H.D.	_	-45	-35	dBc	Vapc = controlled,
Input VSWR	VSWR (in)	—	1.5	3	—	$R_{L} = Rg = 50$, $Tc = 25^{\circ}C$
Output power (1)	Pout (1)	35.5	36.0	_	dBm	$\label{eq:VD} \begin{array}{l} \mbox{Pin} = 0 \ \mbox{dBm}, \ \mbox{V}_{\mbox{\tiny DD}} = 3.5 \ \mbox{V}, \\ \mbox{V}_{\mbox{\tiny APC}} = 2.2 \ \mbox{V}, \ \mbox{R}_{\mbox{\tiny L}} = \mbox{Rg} = 50 , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array}$
Output power (2)	Pout (2)	33.5	34.2	—	dBm	$\label{eq:prod} \begin{array}{l} \mbox{Pin} = 0 \mbox{ dBm}, V_{_{DD}} = 3.0 \mbox{ V}, \\ V_{_{APC}} = 2.2 \mbox{ V}, \mbox{ R}_{_{L}} = \mbox{ Rg} = 50 \mbox{ ,} \\ \mbox{ Tc} = 85^{\circ}\mbox{C} \end{array}$
Isolation	_	_	-40	-36	dBm	$\label{eq:prod} \begin{array}{l} \mbox{Pin} = 0 \mbox{ dBm}, \ \mbox{V}_{_{DD}} = 3.5 \ \mbox{V}, \\ \mbox{V}_{_{APC}} = 0.5 \ \mbox{V}, \ \mbox{R}_{_{L}} = \mbox{R}g = 50 , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array}$
Switching time	tr, tf		1	2	μs	$\begin{array}{l} \text{Pin} = 0 \text{ dBm}, \text{ V}_{_{\text{DD}}} = 3.5 \text{ V}, \\ \text{Pout} = 0 \text{ to } 35.5 \text{ dBm}, \\ \text{R}_{_{\text{L}}} = \text{Rg} = 50 , \text{Tc} = 25^{\circ}\text{C} \end{array}$
Stability	_	No parasitic oscillation			$\begin{array}{l} \mbox{Pin}=0\mbox{ dBm},\mbox{ V}_{\mbox{\tiny DD}}=3\mbox{ to }5.1\mbox{ V},\\ \mbox{Pout} 35.5\mbox{ dBm},\\ \mbox{Vapc} 2.2\mbox{ V}\mbox{ GSM}\mbox{ pulse}.\\ \mbox{Rg}=50\ ,\mbox{ Tc}=25\mbox{°C},\\ \mbox{Output}\mbox{ VSWR}=6:1\mbox{ All phases} \end{array}$	
Load VSWR tolerance		No degradation				$\begin{array}{l} \mbox{Pin}=0\mbox{ dBm},\mbox{ V}_{\mbox{\tiny DD}}=3\mbox{ to }5.1\mbox{ V},\\ \mbox{Pout} 35.5\mbox{ dBm},\\ \mbox{Vapc} 2.2\mbox{ V}\mbox{ GSM}\mbox{ pulse}.\\ \mbox{Rg}=50\ ,\mbox{ t}=20\mbox{ sec.},\mbox{ Tc}=25^{\circ}\mbox{C},\\ \mbox{Output}\mbox{ VSWR}=10:1\mbox{ All phases} \end{array}$

Electrical Characteristics ($Tc = 25^{\circ}C$)

Package Dimensions



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